

3SK285

Silicon N-Channel MOS

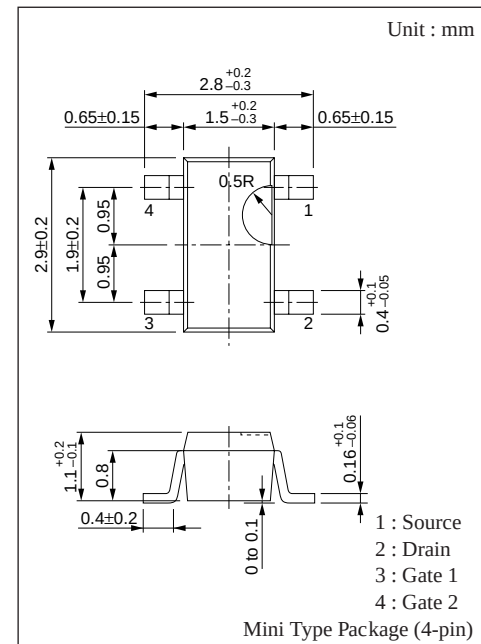
For UHF amplification

■ Features

- Low noise-figure (NF)
- Large power gain PG
- Downsizing of sets by mini power package and automatic insertion by taping/magazine packing are available.

■ Absolute Maximum Ratings (Ta = 25°C)

Parameter	Symbol	Rating	Unit
Drain-Source voltage	V_{DS}	13	V
Gate 1-Source voltage	V_{G1S}	± 8	V
Gate 2-Source voltage	V_{G2S}	± 8	V
Drain current	I_D	± 30	mA
Allowable power dissipation	P_D	150	mW
Channel temperature	T_{ch}	150	°C
Storage temperature	T_{stg}	- 55 to +150	°C



■ Electrical Characteristics (Ta = 25°C)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Drain current	I_{DS}	$V_{DS}=10V, V_{G1S}=1V, V_{G2S}= 4V$	10	18	25	mA
Gate 1 cut-off current	I_{G1SS}	$V_{DS}=V_{G2S}= 0, V_{G1S}= \pm 8V$			± 20	nA
Gate 2 cut-off current	I_{G2SS}	$V_{DS}=V_{G1S}= 0, V_{G2S}= \pm 8V$			± 20	nA
Gate 1-Source cut-off voltage	V_{G1SC}	$V_{DS}=10V, V_{G2S}= 4V, I_D= 0.1mA$	-1		1	V
Gate 2-Source cut-off voltage	V_{G2SC}	$V_{DS}=10V, V_{G1S}= 4V, I_D= 0.1mA$	0		1	V
Drain-Source voltage	V_{DSX}	$I_D= 50\mu A, V_{G1S}= -5V, V_{G2S}= 0$	15			V
Forward transadmittance	$ Y_{fs} $	$V_{DS}=10V, I_D=10mA, V_{G2S}= 4V, f=1kHz$	24	29	34	mS
Input capacitance	C_{iss}	$V_{DS}=10V, V_{G1S}= V_{G2S}= -5V, f=1MHz$	1.4	1.7	2.2	pF
Output capacitance	C_{oss}			0.9	1.2	pF
Feedback capacitance	C_{rss}			0.02		pF
Power gain	PG	$V_{DS}= 8V, I_D= 8mA, V_{G2S}= 3V, f= 800MHz$	15.8	17.5	20	dB
Noise figure	NF			2.2	2.7	dB

■ Marking

Part Number

